



### **60V N-Channel Enhancement Mode MOSFET**

Voltage

60 V

Current

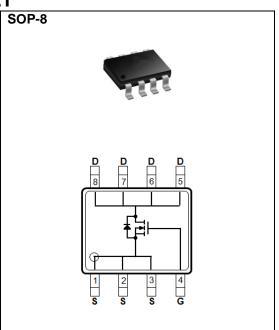
8.3 A

#### **Features**

- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@8.3A<17m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@4.5V$ ,  $I_{D}@4.0A<20m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

- Case: SOP-8 package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0029 ounces, 0.083 grams



### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		$V_{DS}$	60		
Gate-Source Voltage		V <sub>GS</sub> <u>+</u> 20		V	
Continuous Drain Current	T <sub>A</sub> =25°C	l <sub>D</sub>	8.3		
	T <sub>A</sub> =70°C		6.6	Α	
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	33.2	ı	
Power Dissipation	T <sub>A</sub> =25°C	P <sub>D</sub>	2.5	147	
	T <sub>A</sub> =70°C		1.6	W	
Single Pulse Avalanche Energy (Note 5)		E <sub>AS</sub>	45	mJ	
Operating Junction and Storage Temperature Range		$T_{J}$ , $T_{STG}$	-55~150	°C	
Typical Thermal Resistance - Junction to Ambient (Note 6)		$R_{ heta JA}$	50	°C/W	





### **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1.0 1.7 2.5	V				
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =8.3A	-	14	17	mΩ		
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS}$ =4.5V, $I_{D}$ =4A	-	16	20			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	1.0	uA		
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA		
Dynamic (Note 7)								
Total Gate Charge	$Q_g$	V 20V I 0.2A	-	13.5	-	nC		
Gate-Source Charge	$Q_gs$	$V_{DS}=30V, I_{D}=8.3A,$ $V_{GS}=4.5V$ (Note 1,2)	-	4.8	-			
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =4.5 V	-	4.9	-			
Input Capacitance	Ciss	\/ -25\/ \/ -0\/	-	1574	-	pF ns		
Output Capacitance	Coss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	118	-			
Reverse Transfer Capacitance	Crss		-	77	-			
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DD}$ =15V, $I_{D}$ =1A, $V_{GS}$ =10V, $R_{G}$ =6 $\Omega$ (Note 1,2)	-	11	-			
Turn-On Rise Time	tr		-	11	-			
Turn-Off Delay Time	td <sub>(off)</sub>		-	35	-			
Turn-Off Fall Time	tf		-	8.1	-			
Drain-Source Diode								
Maximum Continuous Drain-Source	l <sub>s</sub>		-	-	8.3	А		
Diode Forward Current	IS							
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.68	1	V		

#### NOTES:

- 1. Pulse width<300us, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 5. The test condition is L=0.1mH,  $I_{AS}$ =30A,  $V_{DD}$ =25V,  $V_{GS}$ =10V
- 6. Rejua is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 7. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

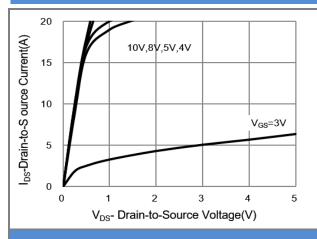


Fig.1 On-Region Characteristics

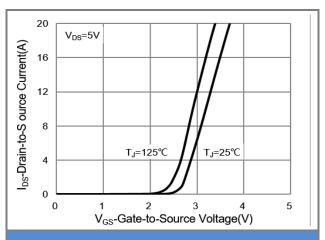


Fig.2 Transfer Characteristics

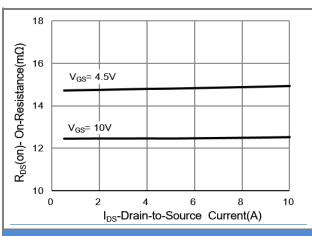


Fig.3 On-Resistance vs. Drain Current

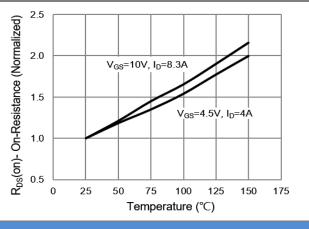


Fig.4 On-Resistance vs. Junction temperature

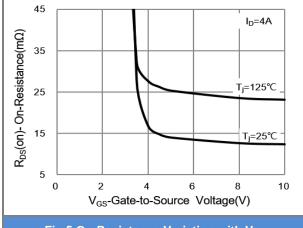
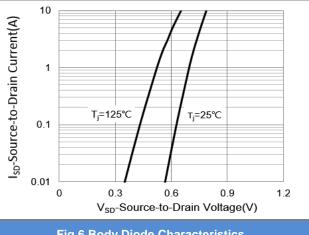


Fig.5 On-Resistance Variation with V<sub>GS</sub>



**Fig.6 Body Diode Characteristics** 





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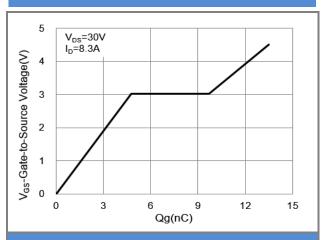


Fig.7 Gate-Charge Characteristics

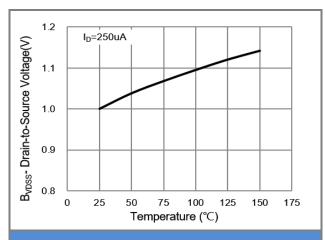


Fig.8 Breakdown Voltage Variation vs. Temperature

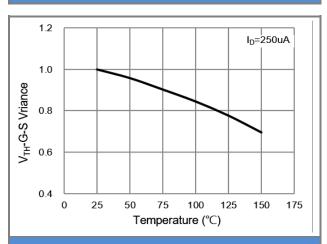


Fig.9 Threshold Voltage Variation with Temperature

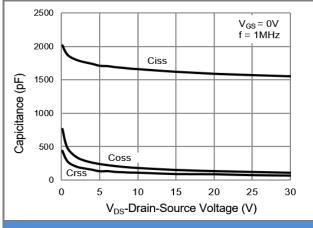
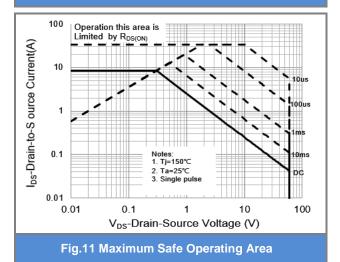


Fig.10 Capacitance vs. Drain-Source Voltage







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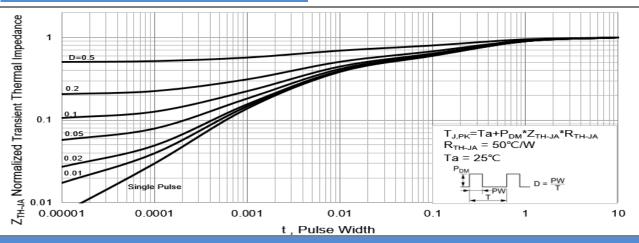


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

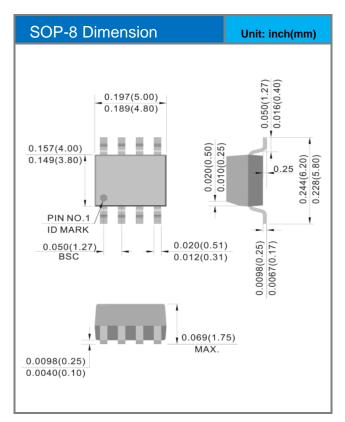


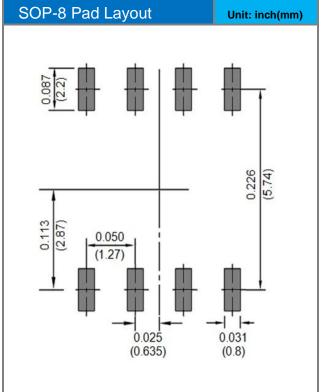


### **Part No Packing Code Version**

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJL9436A1_R2_00001	SOP-8	2.5K pcs / 13" reel	L9436A1	Halogen free

### **Packaging Information & Mounting Pad Layout**









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